National Semiconductor Corporation

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DM85S06 Open-Collector DM75S07/DM85S07 TRI-STATE® DM75S07A/DM85S07A High Speed TRI-STATE Non-Inverting, 64-Bit (16 x 4) RAMs

General Description

These 64-bit active-element memories are monolithic Schottky-clamped transistor-transistor logic (TTL) arrays organized as 16 words of 4 bits each. They are fully decoded and feature a chip-enable input to simplify decoding required to achieve the desired system organization. The memories feature PNP input transistors that reduce the low level input current requirement to a maximum of −0.25 mA, only one-eighth that of a DM54S/DM74S standard load factor. The chip-enable circuitry is implemented with minimal delay times to compensate for added system decoding.

The TRI-STATE output combines the convenience of an open-collector with the speed of a totem-pole output; it can be bus-connected to other similar outputs; yet it retains the fast rise time characteristics of the TTL totem-pole output. Systems utilizing data bus lines with a defined pull-up impedance can employ the open-collector DM85S06.

Write Cycle: The information at the data input is written into the selected location when both the chip-enable input and the read/write input are low. While the read/write input is low, the outputs are in the high-impedance state. When a number of the DM85S07 outputs are bus-connected, this high-impedance state will neither load nor drive the bus line, but it will allow the bus line to be driven by another active output or a passive pull-up if desired.

Read Cycle: The stored information is available at the outputs when the read/write input is high and the chip-enable is low. When the chip-enable is high, the outputs will be in the high-impedance state.

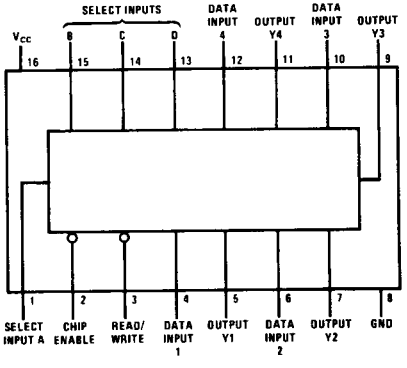
The fast access time of the DM75S07A makes it particularly attractive for implementing high-performance memory functions requiring access times less than 25 ns. The high capacitive drive capability of the outputs permits expansion without additional output buffering. The unique functional capability of the DM75S07 outputs being at a high-impedance during writing, combined with the data inputs being inhibited during reading, means that both data inputs and outputs can be connected to the data lines of a bus-organized system without the need for interface circuits.

Features

- Schottky-clamped for high speed applications (75S07A)
  - Access from chip-enable input 17 ns max
  - Access from address inputs 25 ns max
- TRI-STATE outputs drive bus-organized systems and/or high capacitive loads
- DM85S06 is functionally equivalent and has open-collector outputs
- DM75SXX is guaranteed for operation over the full military temperature range of −55°C to +125°C
- Compatible with most TTL logic circuits
- Chip-enable input simplifies system decoding

Connection Diagram

Dual-In-Line Package



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Top View

Truth Table

Function	Inputs		Output
	Chip-Enable	Read/Write	
Write	L	L	High-Impedance
Read	L	H	Stored Data
Inhibit	H	X	High-Impedance

H = High Level, L = Low Level, X = Don't Care

Order Number DM75S07J, DM75S07AJ, DM85S06J, DM85S07J, DM85S07AJ, DM85S06N, DM85S07N or DM85S07AN
See NS Package Number J16A or N16E

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature Range	−65°C to +150°C
Lead Temperature (Soldering, 10 sec.)	+300°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})			
DM75S07(A)	4.5	5.5	V
DM85S06/DM85S07(A)	4.75	5.25	V
Temperature (T_A)			
DM75S07(A)	−55	+125	°C
DM85S06/DM85S07(A)	0	+70	°C

DM85S06, DM75S07/DM85S07, DM75S07A/DM85S07A Electrical Characteristics

over recommended operating free-air temperature range unless otherwise noted (Notes 2 and 3)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
V_{IH}	High Level Input Voltage			2			V
V_{IL}	Low Level Input Voltage					0.8	V
V_{OH}	High Level Output Voltage	V_{CC} = Min	I_{OH} = −2.0 mA, DM75S07(A)	2.4	3.4		V
			I_{OH} = −5.2 mA, DM85S07(A)	2.4	3.2		V
I_{CEX}	High Level Output Current Open-Collector Only	V_{CC} = Min	V_{OH} = 2.4V			40	μA
			V_{OH} = 5.5V			100	μA
V_{OL}	Low Level Output Voltage	V_{CC} = Min	I_{OL} = 16 mA			0.45	V
			I_{OL} = 20 mA			0.5	V
I_{IH}	High Level Input Current	V_{CC} = Max, V_I = 2.4V				10	μA
I_I	High Level Input Current at Maximum Voltage	V_{CC} = Max, V_I = 5.5V				1.0	mA
I_{IL}	Low Level Input Current	V_{CC} = Max, V_I = 0.40V				−250	μA
I_{OS}	Short Circuit Output Current (Note 4)	V_{CC} = Max, V_O = 0V DM75S07(A), DM85S07(A)		−30		−90	mA
I_{CC}	Supply Current (Note 5)	V_{CC} = Max			75	100	mA
V_{IC}	Input Clamp Voltage	V_{CC} = Min, I_I = −18 mA				−1.2	mA
I_{OZH}	TRI-STATE Output Current, High Level Voltage Applied	V_{CC} = Max, V_O = 2.4V DM75S07(A), DM85S07(A)				40	μA
I_{OZL}	TRI-STATE Output Current, Low Level Voltage Applied	V_{CC} = Max, V_O = 0.4V DM75S07(A), DM85S07(A)		−40			μA
C_{IN}	Input Capacitance	V_{CC} = 5V, V_{IN} = 2V, T_A = 25°C, 1 MHz			4		pF
C_O	Output Capacitance	V_{CC} = 5V, V_O = 2V, T_A = 25°C, 1 MHz Output "Off"			6		pF

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DM75S07/DM85S07 Switching Characteristics

over recommended operating ranges of T_A and V_{CC} unless otherwise noted

Symbol	Parameter		Conditions	DM75S07			DM85S07			Units
				Min	Typ (Note 1)	Max	Min	Typ (Note 1)	Max	
t_{AA}	Access Time from Address		C_L = 30 pF, R_L = 280Ω *(Figure 4)*		25	50		25	35	ns
t_{CZH}	Output Enable Time to High Level	Access Times from Chip-Enable			12	25		12	17	ns
t_{CZL}	Output Enable Time to Low Level				12	25		12	17	ns
t_{WZH}	Output Enable Time to High Level	Sense Recovery Times from Read/Write			13	35		13	25	ns
t_{WZL}	Output Enable Time to Low Level				13	35		13	25	ns
t_{CHZ}	Output Disable Time from High Level	Disable Times from Chip-Enable	C_L = 5 pF, R_L = 280Ω *(Figure 4)*		12	25		12	17	ns
t_{CLZ}	Output Disable Time from Low Level				12	25		12	17	ns
t_{WHZ}	Output Disable Time from High Level	Disable Times from Read/Write			15	35		15	25	ns
t_{WLZ}	Output Disable Time from Low Level				15	35		15	25	ns
t_{WP}	Width of Write Enable Pulse (Read/Write Low)			25			25			ns
t_{ASW}	Set-Up Time *(Figure 1)*	Address to Read/Write		0			0			ns
t_{DSW}		Data to Read/Write		25			25			ns
t_{CSW}		Chip-Enable to Read/Write		0			0			ns
t_{AHW}	Hold Time *(Figure 1)*	Address from Read/Write		0			0			ns
t_{DHW}		Data from Read/Write		0			0			ns
t_{CHW}		Chip-Enable from Read/Write		0			0			ns

DM75S07A/DM85S07A Switching Characteristics

over recommended operating ranges of T_A and V_{CC} unless otherwise noted

Symbol	Parameter		Conditions	DM75S07A			DM85S07A			Units
				Min	Typ (Note 1)	Max	Min	Typ (Note 1)	Max	
t_{AA}	Access Time from Address		C_L = 30 pF, R_L = 280Ω *(Figure 4)*		20	30		20	25	ns
t_{CZH}	Output Enable Time to High Level	Access Times from Chip-Enable			12	25		12	17	ns
t_{CZL}	Output Enable Time to Low Level				12	25		12	17	ns
t_{WZH}	Output Enable Time to High Level	Sense Recovery Times from Read/Write			13	35		13	25	ns
t_{WZL}	Output Enable Time to Low Level				13	35		13	25	ns
t_{CHZ}	Output Disable Time from High Level	Disable Times from Chip-Enable	C_L = 5 pF, R_L = 280Ω *(Figure 4)*		12	25		12	17	ns
t_{CLZ}	Output Disable Time from Low Level				12	25		12	17	ns
t_{WHZ}	Output Disable Time from High Level	Disable Times from Read/Write			15	35		15	25	ns
t_{WLZ}	Output Disable Time from Low Level				15	35		15	25	ns
t_{WP}	Width of Write Enable Pulse (Read/Write Low)			25			20			ns
t_{ASW}	Set-Up Time *(Figure 1)*	Address to Read/Write		0			0			ns
t_{DSW}		Data to Read/Write		25			20			ns
t_{CSW}		Chip-Enable to Read/Write		0			0			ns
t_{AHW}	Hold Time *(Figure 1)*	Address from Read/Write		0			0			ns
t_{DHW}		Data from Read/Write		0			0			ns
t_{CHW}		Chip-Enable from Read/Write		0			0			ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the −55°C to +125°C temperature range for the DM75S07(A) and across the 0°C to +70°C range for the DM85S07(A). All typicals are given for V_{CC} = 5.0V and T_A = 25°C.

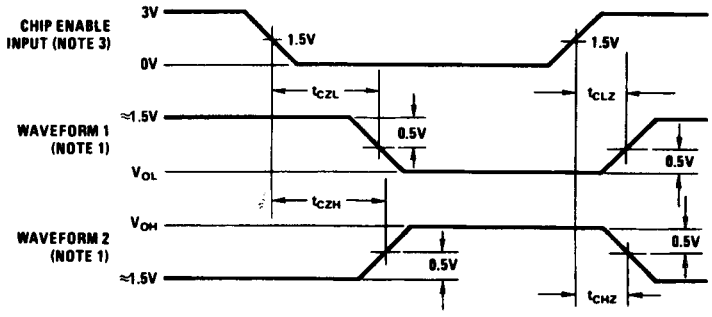
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: I_{CC} is measured with all inputs grounded; and the outputs open.

DM75S07(A)/DM85S07(A) Switching Time Waveforms

Enable and Disable Time from Chip-Enable



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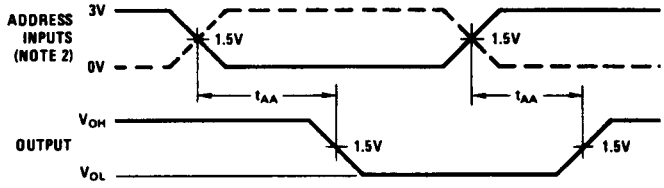
Access Time from Address Inputs



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Write Cycle

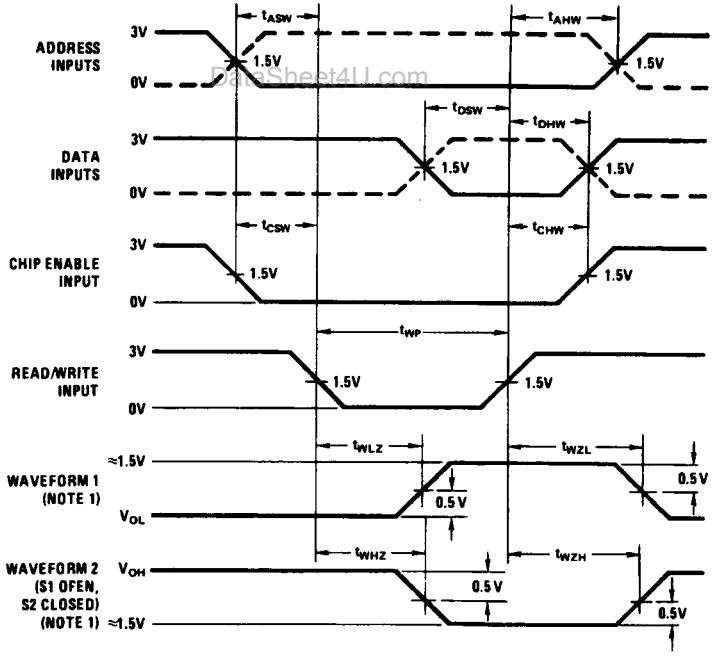

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FIGURE 1

Note 1: Waveform 1 is for the output with internal conditions such that the output is low except when disabled. Waveform 2 is for the output with internal conditions such that the output is high except when disabled.

Note 2: When measuring delay times from address inputs, the chip-enable input is low and the read/write input is high.

Note 3: When measuring delay times from chip-enable input, the address inputs are steady-state and the read/write input is high.

Note 4: Input waveforms are supplied by pulse generators having the following characteristics: $t_r \leq 2.5$ ns, $t_f \leq 2.5$ ns, PRR ≤ 1 MHz and $Z_{OUT} = \approx 50\Omega$.

DM75S06/DM85S06 Switching Characteristics

over recommended operating ranges of T_A and V_{CC} unless otherwise noted

Symbol	Parameter		Conditions	DM75S06			DM85S06			Units
				Min	Typ (Note 1)	Max	Min	Typ (Note 1)	Max	
t_{AA}	Access Times from Address		C_L = 30 pF, R_{L1} = 300Ω, R_{L2} = 600Ω *(Figure 4)*		25	50		25	35	ns
t_{CHL}	Enable Time from Chip-Enable				12	25		12	17	ns
t_{WHL}	Enable Time from Read/Write	Sense Recovery Time from Read/Write			13	35		13	25	ns
t_{CLH}	Disable Time from Chip-Enable				12	25		12	20	ns
t_{WLH}	Disable Time from Read/Write				13	35		13	25	ns
t_{WP}	Width of Write Enable Pulse (Read/Write Low)			25			25			ns
t_{ASW}	Set-Up Time *(Figure 2)*	Address to Read/Write		0			0			ns
t_{DSW}		Data to Read/Write		25			25			ns
t_{CSW}		Chip-Enable to Read/Write		0			0			ns
t_{AHW}	Hold Time *(Figure 2)*	Address from Read/Write		0			0			ns
t_{DHW}		Data from Read/Write		0			0			ns
t_{CHW}		Chip-Enable from Read/Write		0			0			ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the −55°C to +125°C temperature range for the DM75S07(A) and across the 0°C to +70°C range for the DM85S07(A). All typicals are given for V_{CC} = 5.0V and T_A = 25°C.

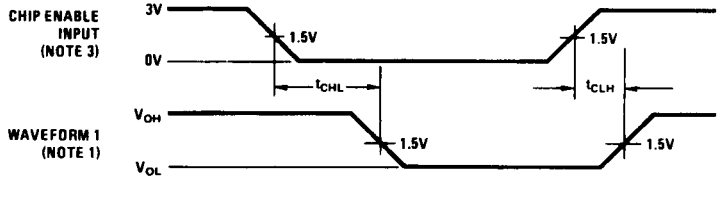
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: I_{CC} is measured with all inputs grounded; and the outputs open.

DM75S06/DM85S06 Switching Time Waveforms

Enable and Disable Time from Chip-Enable



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Access Time from Address Inputs

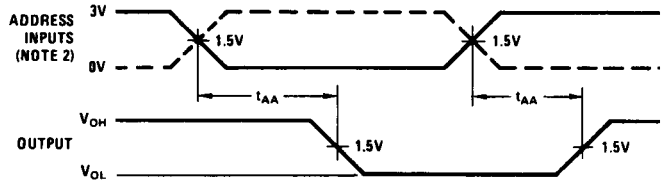

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FIGURE 2

DM75S06/DM85S06 Switching Time Waveforms (Continued)

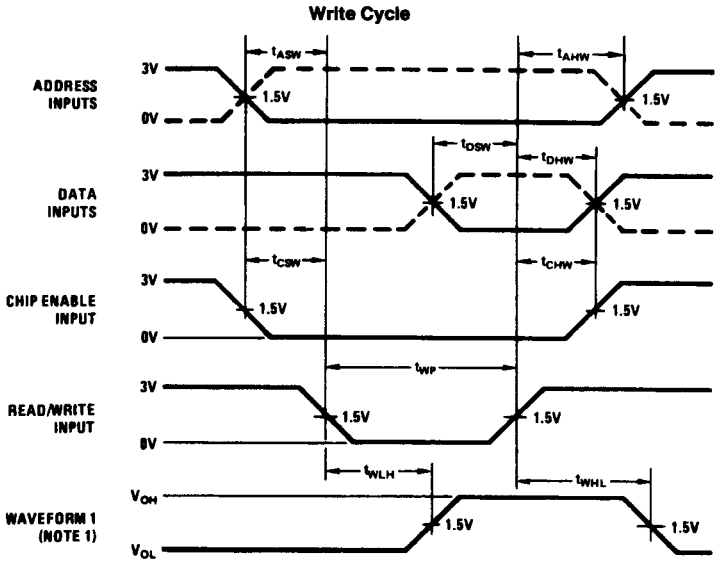

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FIGURE 2 (Continued)

Note 1: Waveform 1 is for the output with internal conditions such that the output is low except when disabled.

Note 2: When measuring delay times from address inputs, the chip-enable input is low and the read/write input is high.

Note 3: When measuring delay times from chip-enable input, the address inputs are steady-state and the read/write input is high.

Note 4: Input waveforms are supplied by pulse generators having the following characteristics: $t_r \leq 2.5$ ns, $t_f \leq 2.5$ ns, PRR ≤ 1 MHz and $Z_{OUT} \approx 50\Omega$.

Block Diagram

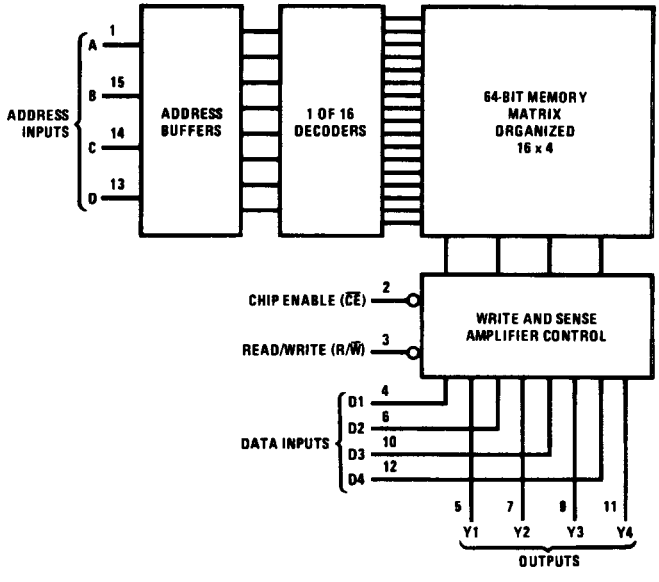

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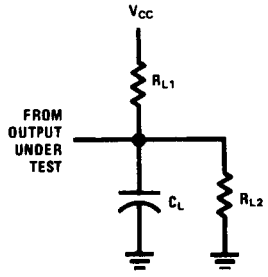
FIGURE 3

AC Test Circuits

DM75S06/DM85S06



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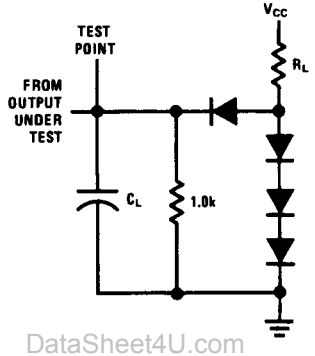
DM75S07(A)/DM85S07(A)



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C_L includes probe and jig capacitance.
All diodes are 1N3064.

FIGURE 4